Priority Number(s): Requested Patent: Equivalents: EC Classification: IPC Classification: Application Applicant(s):: Inventor(s): Publication date: Patent Number: MANUFACTURE OF SEMICONDUCTOR DEVICE PACKAGE H01L23/12; H01L21/56; H01L23/48 SONY KK JP1760995C, JP4047977B JP19830083188 19830512 ☐ <u>JP59208756</u> AKIYAMA KATSUHIKO; others: 02 JP59208756 1984-11-27 Abstract

solution from the back surface 11a to complete a leadless type package 21. Bottom surfaces of the Au layers are used as external electrodes 12b, of 35mum thickness. A semiconducor chip 15 is mounted 16 on a portion 11g and connected 19 to external electrodes 17, 18 on the portions 11h, soldered to a conductor pattern on the substrate. With this constitution, a package of excellent heat radiation can be manufactured automatically by 11i. The transfer-molding with epoxy resin 20 is carried out so as to make thickness t=1mm. The Fe substrate is removed by etching with FeCI3 an easy and simple method. 12c and the heat radiation surface 12a. In other to mount the package 21 on a printed circuit board, only the external electrodes 12b, 12c are directly

substrate is selectively removed by etching.

wherein the semiconductor device is mounted on a substrate and, after being connected to external electrodes, enclosed integrally with resin and the

PURPOSE:To obtain a semiconductor device package which is excellent in heat radiation and suitable for automated manufacturing by a method

CONSTITUTION:Au plating 12 of 1mum thickness, Ni plating 13 of 1mum thickness and Au plating 14 of 3mum are laminated on an Fe substrate 11

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